

Eunah Ko

List of Publications by Year in descending order

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11
papers

375
citations

1307594

7
h-index

1372567

10
g-index

11
all docs

11
docs citations

11
times ranked

412
citing authors

#	ARTICLE	IF	CITATIONS
1	Negative Capacitance FinFET With Sub-20-mV/decade Subthreshold Slope and Minimal Hysteresis of 0.48 V. IEEE Electron Device Letters, 2017, 38, 418-421.	3.9	100
2	Vertical Tunnel FET: Design Optimization With Triple Metal-Gate Layers. IEEE Transactions on Electron Devices, 2016, 63, 5030-5035.	3.0	90
3	Steep switching devices for low power applications: negative differential capacitance/resistance field effect transistors. Nano Convergence, 2018, 5, 2.	12.1	60
4	Sub-60-mV/decade Negative Capacitance FinFET With Sub-10-nm Hafnium-Based Ferroelectric Capacitor. IEEE Journal of the Electron Devices Society, 2017, 5, 306-309.	2.1	57
5	Steep Slope Silicon-On-Insulator Feedback Field-Effect Transistor: Design and Performance Analysis. IEEE Transactions on Electron Devices, 2019, 66, 286-291.	3.0	33
6	Analysis on the Operation of Negative Differential Resistance FinFET With Pb(Zr _{0.52} Ti _{0.48})O ₃ Threshold Selector. IEEE Transactions on Electron Devices, 2018, 65, 19-22.	3.0	13
7	Super steep-switching (SS $\hat{=}$ 2 mV/decade) phase-FinFET with Pb(Zr _{0.52} Ti _{0.48})O ₃ threshold switching device. Applied Physics Letters, 2018, 113, .	3.3	8
8	Optimization of double metal-gate InAs/Si heterojunction nanowire TFET. Semiconductor Science and Technology, 2020, 35, 075024.	2.0	8
9	Effective drive current in steep slope FinFET (vs. conventional FinFET). Applied Physics Letters, 2017, 111, .	3.3	5
10	Steep Slope Silicon-on-Insulator Field Effect Transistor with Negative Capacitance: Analysis on Hysteresis. Journal of Nanoscience and Nanotechnology, 2019, 19, 6128-6130.	0.9	1
11	Layout engineering to suppress hysteresis of negative capacitance FinFET. , 2017, , .		0